

R E M A R K S

Claim 2 had previously been canceled. Applicants cancel claim 1. Claims 3-18 remain pending in the application. Applicants amend claim 3 for clarification, amend claim 7 to depend from claim 3, and amend claims 8, 11, and 15 to independent form. No new matter has been added.

Applicants acknowledge with appreciation the Examiner's allowance of claims 4-6 and the finding that claims 8-18 contain allowable subject matter. Accordingly, Applicants amend claims 8, 11, and 15 to independent form, and respectfully request that the Examiner allow claims 8-18. Applicants also respectfully submit that the provided reasons for allowability only include the Examiner's non-exhaustive interpretations, which should in no way limit the scope of the allowable claims.

Claim 1 stands rejected under 35 U.S.C. § 102(b) as being anticipated by Applicants' Admitted Prior Art ("AAPA"); and claims 1, 3, and 7 stand rejected under 35 U.S.C. § 102(e) as being anticipated by U.S. Patent No. 6,611,407 to Chang. Applicants cancel claim 1 and amend claims 3 and 7 in a good faith effort to clarify the invention as distinguished from Chang cited by the Examiner. Applicants respectfully traverse the rejection.

Applicants respectfully submit that Chang, as cited and relied upon by the Examiner, fails to disclose,

"[a] semiconductor integrated circuit device comprising:
a terminal; and
a first capacitance adjusting section which is connected to a
wiring between said terminal and a protection resistor in a front
stage of an internal circuit,
wherein said first capacitance adjusting section adjusts
terminal capacitance of said terminal, based on capacitance of said
first capacitance adjusting section,

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wherein said first capacitance adjusting section comprises a first adjusting capacitor which adjusts said terminal capacitance, and wherein said first adjusting capacitor comprises:

a first semiconductive portion which is composed of a first well region formed in a substrate with said internal circuit and having a conductive type opposite to that of said substrate, [[and]]

a second semiconductive portion which is opposite to said first semiconductive portion and is composed of a first diffusion layer region formed in said first well region and having the same conductive type as that of said substrate, and

a depletion layer formed between said first diffusion layer region and said first well region," as recited in amended claim 3. (Emphasis added)

Accordingly, Applicants respectfully submit that claim 3, together with claim 7 dependent therefrom, is patentable over Chang for at least the above-stated reasons.

The above statements on the disclosure in the cited reference represent the present opinions of the undersigned attorney. The Examiner is respectfully requested to specifically indicate those portions of the reference that provide the basis for a view contrary to any of the above-stated opinions.

Applicants appreciate the Examiner's implicit finding that the additional references made of record, but not applied, do not render the claims of the present application unpatentable, whether these references are considered alone or in combination with others.

In view of the remarks set forth above, this application is in condition for allowance which action is respectfully requested. However, if for any reason the Examiner should consider this application not to be in condition for allowance, the Examiner is respectfully requested to telephone the undersigned attorney at the number listed below prior to issuing a further Action.

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Any fee due with this paper may be charged to Deposit Account No. 50-1290.

Respectfully submitted,



Dexter T. Chang
Reg. No. 44,071

CUSTOMER NUMBER 026304

Telephone: (212) 940-8703

Fax: (212) 940-8986 or 8987

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